



High-Speed Quad SPST CMOS Analog Switch

DESCRIPTION

The DG201HS is an improved monolithic device containing four independent analog switches. It is designed to provide high speed, low error switching of analog signals. Combining low on-resistance (25 Ω) with high speed (t_{ON}: 38 ns), the DG201HS is ideally suited for high speed data acquisition requirements.

To achieve high voltage ratings and superior switching performance, the DG201HS is built on a proprietary high-voltage silicon-gate process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks input voltages to the supply values, when off.

FEATURES

Fast Switching-t_{ON}: 38 ns
Low On-Resistance: 25 Ω

Low Leakage: 100 pALow Charge Injection

- TTL/CMOS Logic Compatible
- Single Supply Compatibility
- High Current Rating: 30 mA

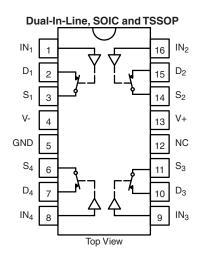
BENEFITS

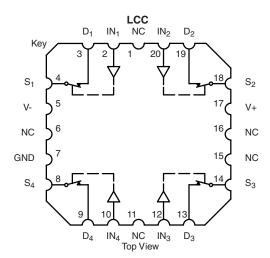
- Faster Throughput
- Higher Accuracy
- · Reduced Pedestal Error
- · Upgrades Existing Designs
- Simple Interfacing
- Replaces HI201HS, ADG201HS
- Space Savings (TSSOP)

APPLICATIONS

- · Data Acquisition
- · Hi-Rel Systems
- Sample-and-Hold Circuits
- Communication Systems
- Automatic Test Equipment
- Integrator Reset Circuits
- Choppers
- Gain Switching
- Avionics

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





TRUTH TABLE				
Logic	Switch			
0	ON			
1	OFF			

 $\begin{array}{l} Logic \ "0" \leq 0.8 \ V \\ Logic \ "1" \geq 2.4 \ V \end{array}$

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

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RDERING INFORMATION				
Temp Range	Package	Part Number		
	16-Pin Plastic DIP	DG201HSDJ DG201HSDJ-E3		
- 40 to 85 °C	16-Pin Narrow SOIC	DG201HSDY DG201HSDY-E3 DG201HSDY-T1 DG201HSDY-T1-E3		
	16-Pin TSSOP	DG201HSDQ DG201HSDQ-E3 DG201HSDQ-T1 DG201HSDQ-T1-E3		

ABSOLUTE MAXIMUM	RATINGS			
Parameter		Limit	Unit	
V+ to V-		44		
GND to V-		25	J	
Digital Inputs ^a , V _S , V _D		(V-) - 4 to (V+) + 4 or 30 mA, whichever occurs first		
Continuous Current (Any Terminal)		30		
Current, S or D (Pulsed at 1 ms, 10 % duty cycle)		100	mA	
Storage Temperature	(A Suffix)	- 65 to 150	°C	
	(D Suffix)	- 65 to 125		
Power Dissipation (Package) ^b	16-Pin Plastic DIP ^c	470		
	16-Pin CerDIP ^d	900	mW	
	16-Pin Narrow Body SOIC and TSSOP ^e	600	11100	
	LCC-20 ^d	900		

- a. Signals on S_X , D_X , or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 6 mW/°C above 75 °C.
- d. Derate 12 mW/°C above 75 °C.
- e. Derate 7.6 mW/°C above 75 °C.

SCHEMATIC DIAGRAM (TYPICAL CHANNEL)

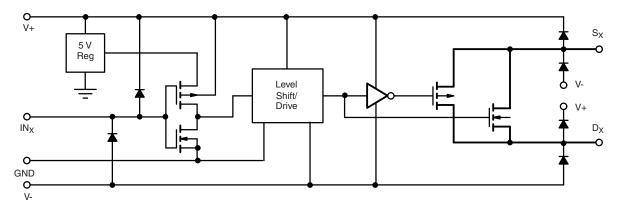


Figure 1.





		Test Conditions			A Suffix		D Suffix		
		Unless Specified			- 55 to 125 °C		- 40 to 85 °C		-
Parameter	Symbol	V+ = 15 V, V- = -15 V $V_{IN} = 3 V, 0.8 V^{f}$	Tempb	Typ ^c	Min ^d	Max ^d	Min ^d	Max ^d	Unit
Analog Switch	Cymbol	- 114 - 2 - 3 - 2 - 2	Temp	1917		IVIUX		INUX	0
Analog Signal Range ^e	V _{ANALOG}		Full		V-	V+	V-	V+	V
Drain-Source		$I_S = -10 \text{ mA}, V_D = \pm 8.5 \text{ V}$	Room	25		50		50	
On-Resistance	r _{DS(on)}	V+ = 13.5 V, V- = - 13.5 V	Full			75		75	Ω
r _{DS(on)} Match			Room	3					%
	I _{S(off)}	V+ = 16.5 V, V- = - 16.5 V	Room	0.1	- 1	1	- 1	1	
Switch Off Leakage Current	-5(011)	$V_D = \pm 15.5 \text{ V}$	Full		- 60	60	- 20	20	-
· ·	I _{D(off)}	$V_{S} = \pm 15.5 \text{ V}$	Room Full	0.1	- 1 - 60	1 60	- 1 - 20	1 20	nA
Channel On Leakage		V+ = 16.5 V, V- = - 16.5 V	Room	0.1	- 1	1	- 1	1	
Current	I _{D(on)}	$V_S = V_D = \pm 15.5 \text{ V}$	Full	0.1	- 60	60	- 20	20	
Digital Control					l	<u> </u>	l	L	ı
Input, High Voltage	V _{INH}		Full		2.4		2.4		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Input, Low Voltage	V _{INL}		Full			0.8		0.8	V
Input Capacitance	C _{IN}		Full	5					рF
Input Current	I _{INH} or I _{INL}	V _{IN} under test = 0.8 V, 3 V	Full		- 1	1	- 1	1	μΑ
Dynamic Characteristics					L				
Turn-On Time	t _{ON}		Room	48		60		60	
Tan on Timo	-014	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$	Full			75		75	-
Turn-Off Time	t _{OFF1}	$V_S = \pm 10 \text{ V}, V_{INH} = 3 \text{ V}$	Room Full	30		50 70		50 70	ns
turn-Oil Time	t _{OFF2}	See Figure 2	Room	150		70		70	
Output Settling Time to 0.1 %	t _s		Room	180					
- Culput Cottining Time to 0.1 70	-5	$C_{I} = 1 \text{ nF, } V_{S} = 0 \text{ V}$	1100111	100					
Charge Injection	Q	$V_{gen} = 0 \text{ V}, R_{gen} = 0 \Omega$	Room	- 5					рС
		$R_L = 1 \text{ k}\Omega, C_L = 10 \text{ pF}$							
Off Isolation	OIRR	f = 100 kHz	Room	85					
Crosstalk		Any Other Channel Switches							dB
(Channel-to-Channel)	X _{TALK}	$R_L = 1 \text{ k}\Omega, C_L = 10 \text{ pF}$	Room	100					
	0	f = 100 kHz							
Source Off Capacitance	C _{S(off)}		Room	8					=
Drain Off Capacitance	C _{D(off)}	V_{S} , $V_{D} = 0$ V, $f = 1$ MHz	Room	8					pF
Channel On Capacitance	C _{D(on)}	\mathbf{v}_{S} , $\mathbf{v}_{D} = 0$ \mathbf{v} , $\mathbf{i} = 1$ ivinz	Room	30					PΓ
Drain-to-Source Capacitance	C _{DS(off)}		Room	0.5					
Power Supplies	LL_								
···	I		Room	4.5					
Positive Supply Current	l+	V+ = 15 V, V- = - 15 V	Full			10		10	mA
Negative Supply Current	I-	V + = 15 V, V - = -15 V $V_{IN} = 0 \text{ or } 5 \text{ V}$	Room	3.5	_		_		''''
		- IIV 3 3. 3 3	Full		- 6	0.10	- 6	0.10	
Power Consumption ^c	P _C		Full			240		240	mW

Notes:

a.Refer to PROCESS OPTION FLOWCHART.

b.Room = 25 °C, Full = as determined by the operating temperature suffix.

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

d.The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

e.Guaranteed by design, not subject to production test.

f. V_{IN} = input voltage to perform proper function.

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SPECIFICATIONS ^a I	FOR SINGL									
		Test Conditions			A Suffix - 55 to 125 °C		D Suffix - 40 to 85 °C			
		Unless Specified $V+ = 10.8 V \text{ to } 16.5 V,$							4	
Parameter	Symbol	$V = 10.0 \text{ V} \cdot 10.3 \text{ V},$ $V = \text{GND} = 0 \text{ V}, \text{V}_{\text{IN}} = 3 \text{ V}, 0.8 \text{ V}^{\text{f}}$	Temp ^b	Тур ^с	Min ^d	Max ^d	Min ^d	Max ^d	Unit	
Analog Switch	 		1.4	- 7		1		1		
Analog Signal Range ^e	V _{ANALOG}		Full		0	V+	0	V+	V	
Drain-Source		I _S = - 10 mA, V _D = 8.5 V	Room	0.5		90		90		
On-Resistance	r _{DS(on)}	V+ = 10.8 V	Full	65		120		120	Ω	
	I _{S(off)}	V+ = 16.5 V	Room	0.1	- 1	1	- 1	1		
Switch Off Leakage Current	3(011)	$V_S = 0.5 \text{ V}, 10 \text{ V}$	Full	• • •	- 60	60	- 20	20		
· ·	I _{D(off)}	$V_D = 10 \text{ V}, 0.5 \text{ V}$	Room Full	0.1	- 1 - 60	1 60	- 1 - 20	1 20	nA	
Channel On Leakage	1 .1	V+ = 16.5 V	Room	0.4	- 1	1	- 1	1	1	
Current	$I_{D(on)} + I_{S(on)}$	$V_D = 0.5 V, 10 V$	Full	0.1	- 60	60	- 20	20		
Digital Control										
Input, High Voltage	V _{INH}		Full		2.4		2.4		V	
Input, Low Voltage	V _{INL}		Full			0.8		0.8	\ \	
Input Capacitance	C _{IN}		Full	5					pF	
Input Current	I _{INH} or I _{INL}	V+ = 16.5 V V _{IN} under test = 0.8 V, 3 V	Full		- 1	1	- 1	1	μΑ	
Dynamic Characteristics	<u> </u>									
Turn-On Time	t _{ON}		Room			50		50		
Turn on Time	ON	ON	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$	Full			70		70	
T 0"T	t_{OFF1} $V_S = 2 \text{ V, V} = 10.8 \text{ V}$ See Figure 2		Room Full			50 70		50 70	ns	
Turn-Off Time		See Figure 2	Room	150		70		70		
Output Settling Time to 0.1 %	t _s		Room	180						
		$C_{I} = 1 \text{ nF, } V_{S} = 0 \text{ V}$	1100111	100						
Charge Injection	Q	$V_{gen} = 0 \text{ V}, R_{gen} = 0 \Omega$	Room	10					рC	
Off Isolation	OIRR	$R_L = 1 \text{ k}\Omega, C_L = 10 \text{ pF}$	Room	85						
On isolation	OIRR	f = 100 kHz	Hoom	65						
Crosstalk		Any Other Channel Switches							dB	
(Channel-to-Channel)	X _{TALK}	$R_L = 1 \text{ k}\Omega, C_L = 10 \text{ pF}$	Room	100						
Source Off Capacitance	C _{S(off)}	f = 100 kHz	Room	10						
Drain Off Capacitance	C _{D(off)}	f = 1 MHz	Room	10					pF	
Channel On Capacitance	C _{D(off)}	V _{ANALOG} = 0 V	Room	30					-	
Power Supply	OD(on)	VANALOG - U V	1100111	30				<u> </u>		
Positive Supply Current	l+		Full			10		10	mA	
	P _C	$V+ = 15 V$, $V_{IN} = 0 \text{ or } 5 V$	Full			150		150	mW	
Power Consumption ^c	1.0		Full			130		150	11177	

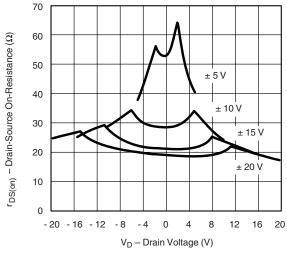
Notes:

- a. Refer to PROCESS OPTION FLOWCHART.
- b.Room = 25 $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e.Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

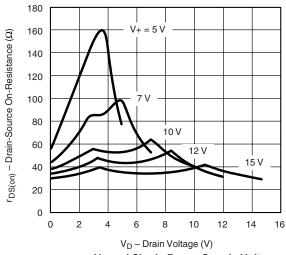
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



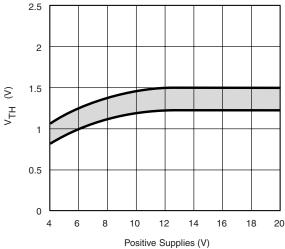
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



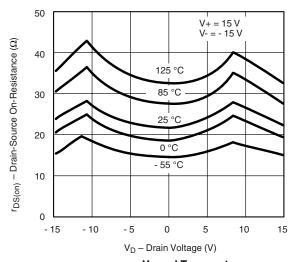
r_{DS(on)} vs. V_D and Power Supply Voltages



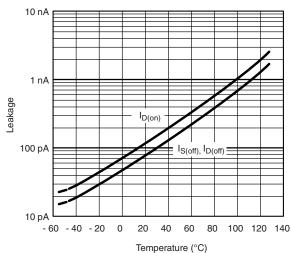
 $r_{\text{DS(on)}}\,\text{vs.}\,\,\text{V}_{\text{D}}$ and Single Power Supply Voltages



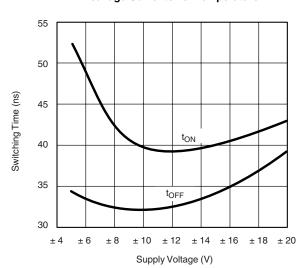
Input Switching Threshold vs. Supply Voltage



 $r_{DS(on)}$ vs. V_D and Temperature



Leakage Currents vs. Temperature

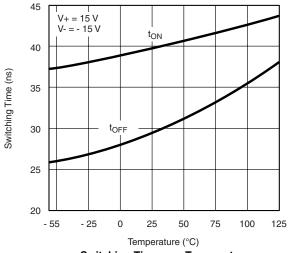


Switching Time vs. Power Supply Voltage

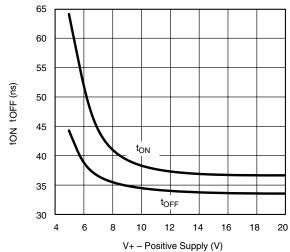
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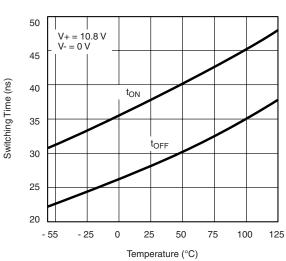
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



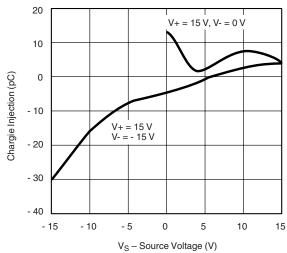
Switching Times vs. Temperature



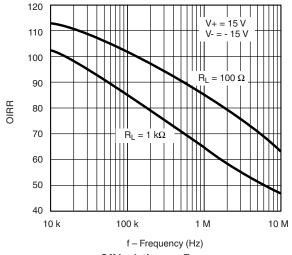
Switching Times vs. Power Supply Voltage



Switching Times vs. Temperature



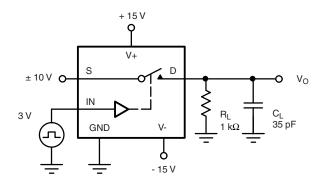
Charge Injection vs. Source Voltage

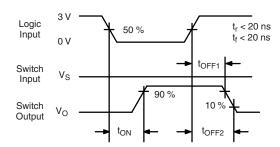


Off Isolation vs. Frequency



TEST CIRCUITS



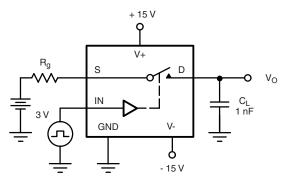


C_L (includes fixture and stray capacitance)

$$V_O = V_S$$

$$\frac{R_L}{R_L + r_{DS(on)}}$$

Figure 2. Switching Time



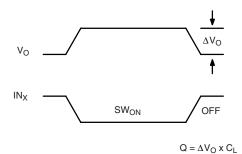
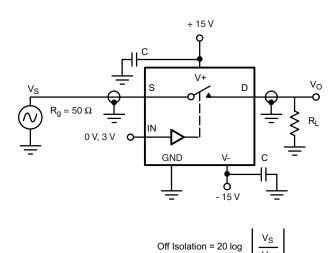


Figure 3. Charge Injection



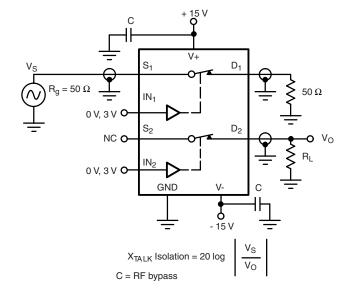


Figure 4. Off Isolation

Figure 5. Crosstalk

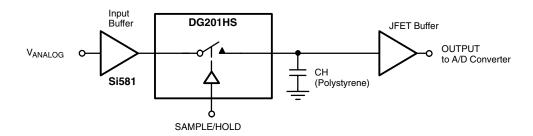
DG201HS

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APPLICATIONS

A high-speed, low-glitch analog switch such as Vishay Siliconix's DG201HS improves the accuracy and shortens the acquisition and settling times of a sample-and-hold circuit.



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